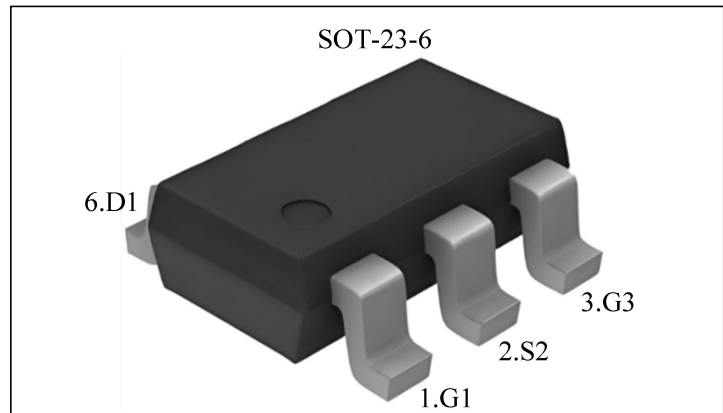


## Dual N-Channel Enhancement Mode Power MOSFET

## Features

- Excellent  $R_{DS(on)}$  and Low Gate Charge
- $V_{DS} = 20V, I_D = 4A$   
 $R_{DS(on)} < 32m\Omega @ V_{GS} = 4.5V$



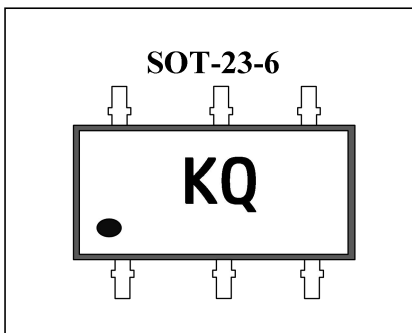
## Mechanical Characteristics

- Package: SOT-23-6
- Packaging: Tape and Reel per EIA 481
- Marking : Making Code

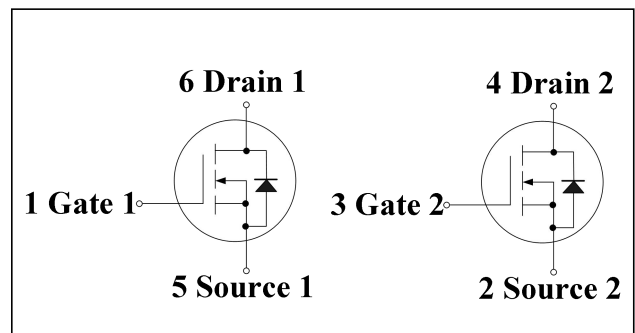
## Applications

- DC/DC Converter
- Load Switch for Portable Devices

## Marking : Making Code



## Schematic Diagram



## Absolute Maximum Rating (Ratings at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbols	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	4	A
Drain Current-Pulsed <sup>Note1</sup>	$I_{DM}$	10	A
Junction Temperature	$P_D$	2	W
Maximum Power Dissipation	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C

## Thermal Characteristics

Thermal Resistance, Junction-to-Ambient Note2	$R_{\theta JA}$	89	°C/W
-----------------------------------------------	-----------------	----	------

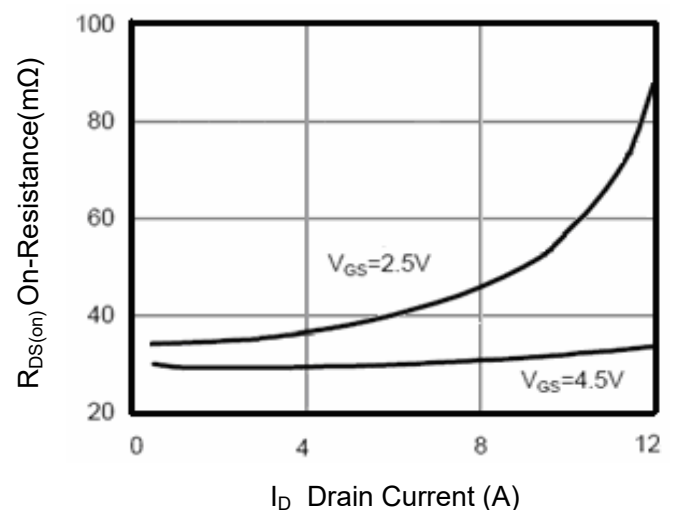
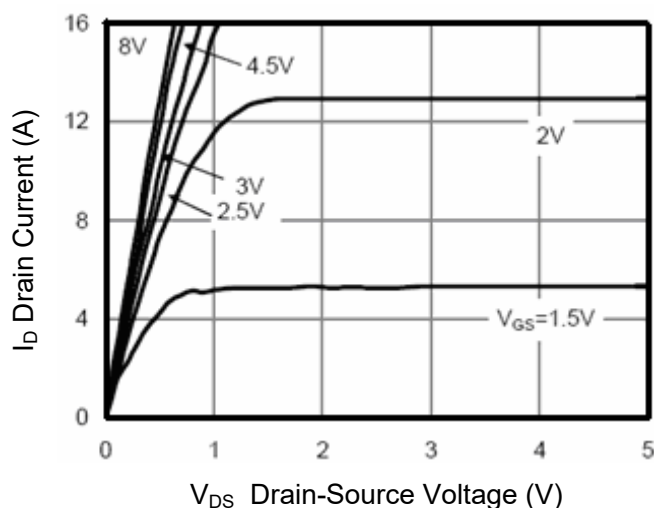
**Electrical Characteristics**(T<sub>c</sub>=25°C Unless otherwise specified)

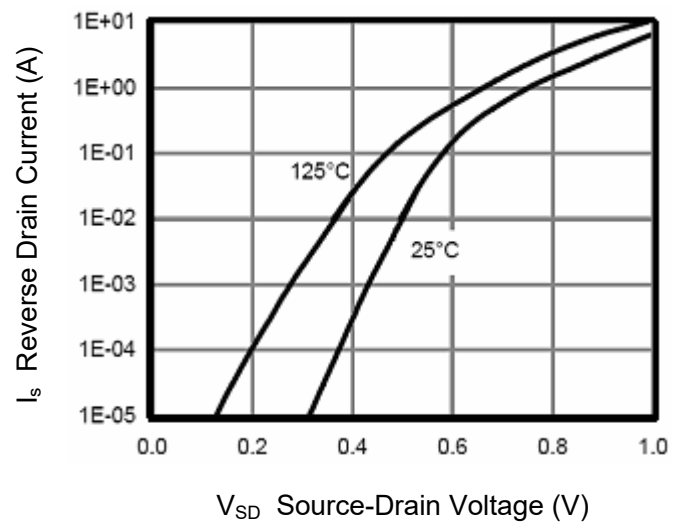
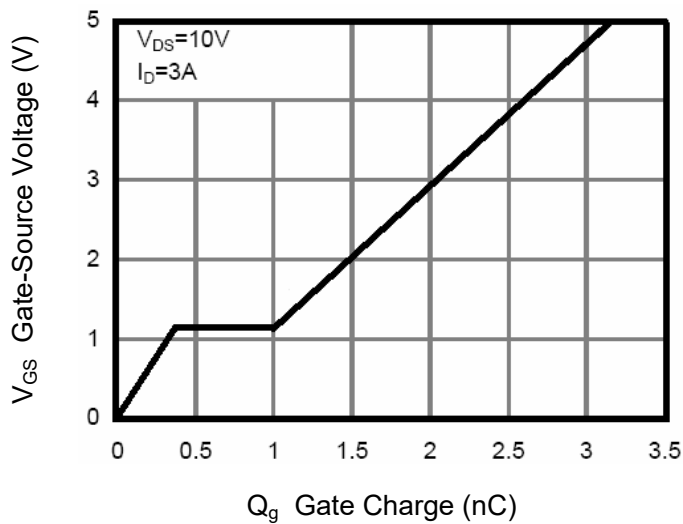
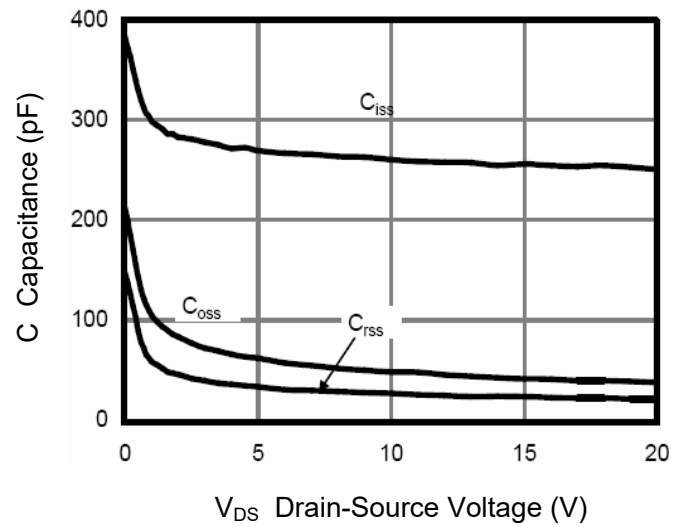
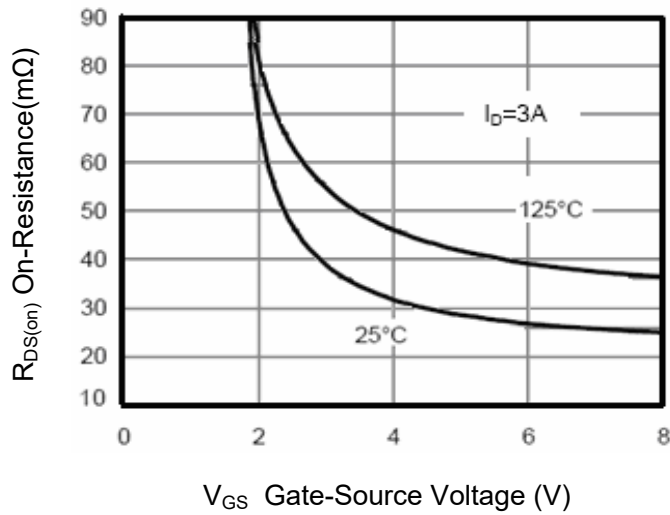
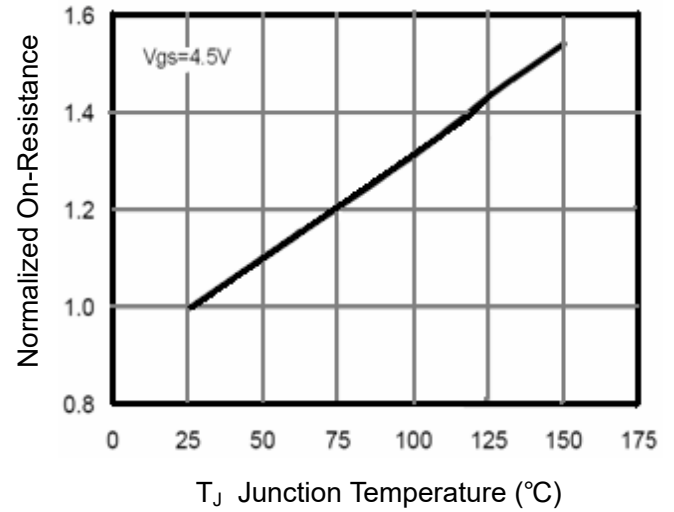
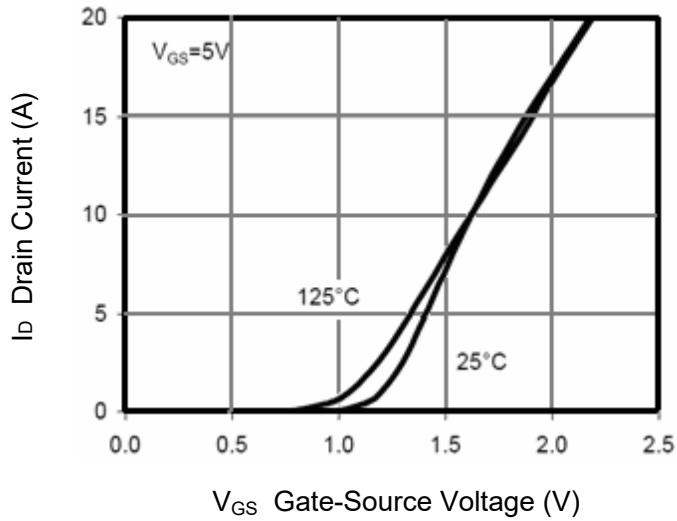
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	--	--	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$	--	--	$\pm 100$	nA
Gate Threshold Voltage <sup>Note3</sup>	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.45	0.7	1	V
Drain-Source On-Resistance <sup>Note3</sup>	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=3A$	--	25	32	m $\Omega$
		$V_{GS}=2.5V, I_D=2A$	--	31	40	m $\Omega$
Forward Transconductance <sup>Note3</sup>	$g_{FS}$	$V_{DS}=5V, I_D=3A$	--	8	--	S
Dynamic Characteristics						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V, f=1MHz$	--	260	--	pF
Output Capacitance	$C_{oss}$		--	48	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	27	--	pF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, V_{GS}=4.5V$ $R_L=3.3\Omega, R_{GEN}=6\Omega$	--	2.5	--	nS
Turn-on Rise Time	$t_r$		--	3.2	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	21	--	nS
Turn-off Fall Time	$t_f$		--	3	--	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4.5V$ $I_D=3A$	--	2.9	--	nC
Gate-Source Charge	$Q_{gs}$		--	0.4	--	nC
Gate-Drain Charge	$Q_{gd}$		--	0.6	--	nC
Source-Drain Diode Characteristics						
Diode Forward Voltage <sup>Note3</sup>	$V_{SD}$	$V_{GS}=0V, I_S=4A$	--	--	1.2	V
Diode Forward Current <sup>Note2</sup>	$I_S$		--	--	4	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

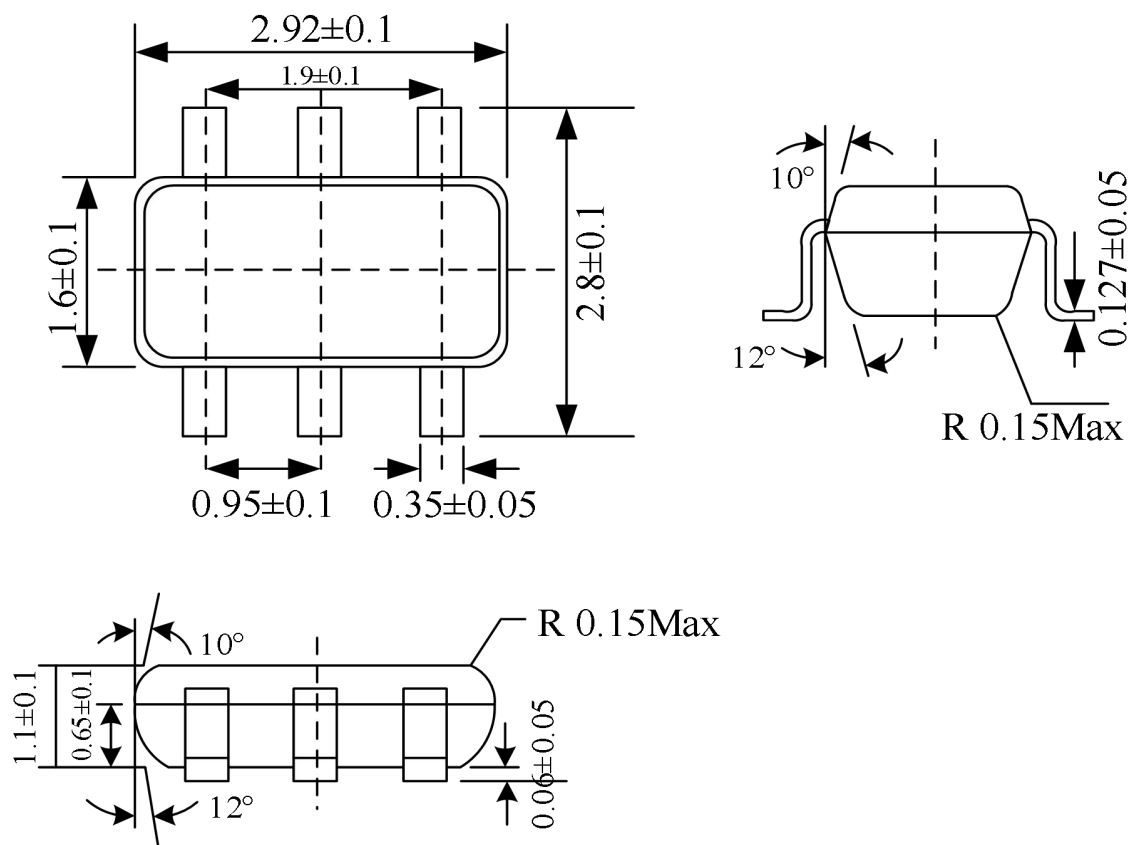
2.Surface Mounted on FR4 Board,  $t \leq 10$  sec.

3.Pulse Test: Pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$

**Typical Characteristics Curves**



## Outline Drawing – SOT-23-6(Dimensions in mm)

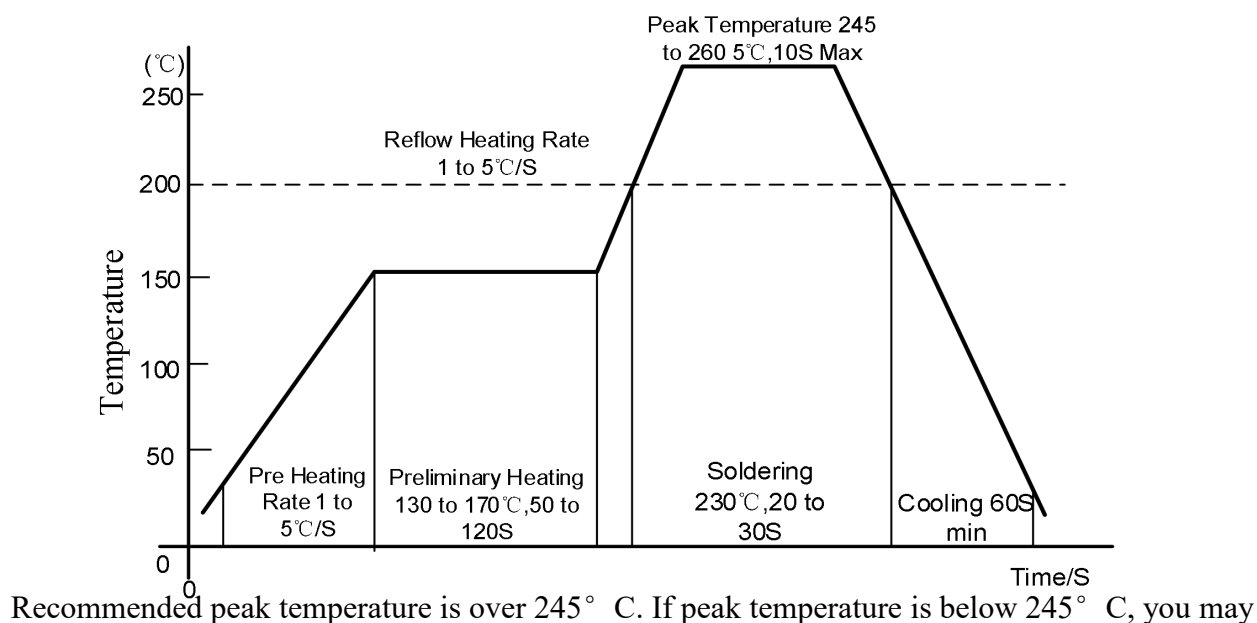


## Package Information

Package Type	Description	Quantity (pcs)	Standard
SOT-23-6	Reel -7 inches	3000	EIA-481

## Conditions of Soldering and Storage

- Recommended condition of reflow soldering



adjust the following parameters:

- |                                            |
|--------------------------------------------|
| • Time length of peak temperature (longer) |
| • Time length of soldering (longer)        |
| • Thickness of solder paste (thicker)      |

• **Conditions of hand soldering**

- |                      |
|----------------------|
| • Temperature: 300°C |
| • Time: 3s max       |
| • Times: one time    |

• **Storage conditions**

- |                                                    |
|----------------------------------------------------|
| • Temperature: 5 to 40° C                          |
| • Humidity: 30 to 80% RH                           |
| • Recommended period: One year after manufacturing |

## Package Specifications

• **The method of packaging**

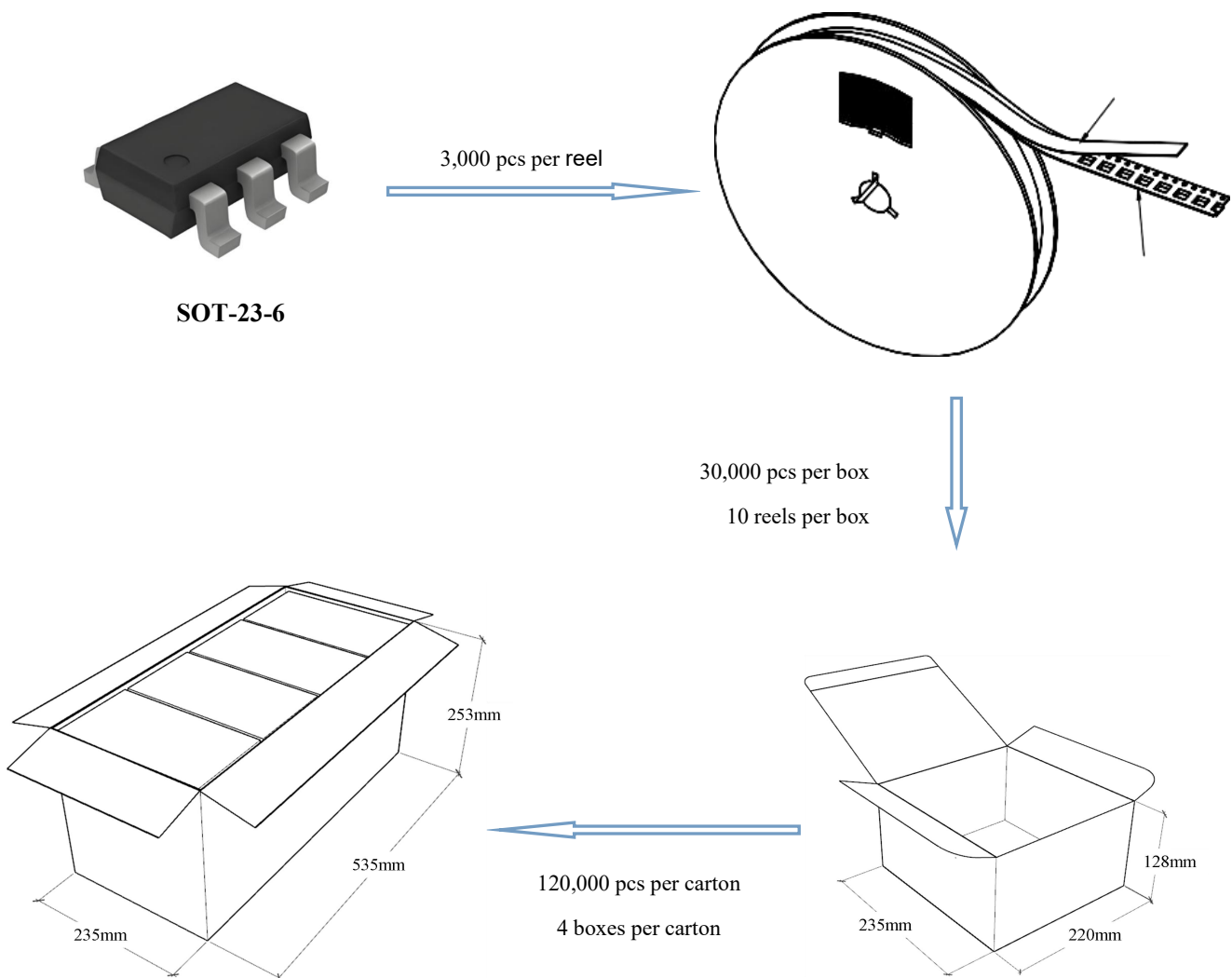


Figure 1 consists of two schematic diagrams of a micro-robot. Diagram (a) is a top-down view showing a circular body with a central hexagonal component labeled 'B' and a rectangular protrusion labeled 'C'. A vertical line labeled 'A' passes through the center. Diagram (b) is a side view showing the vertical profile of the robot. It includes a top section labeled 'D', a bottom section labeled 'E', and a central section labeled 'F' with a hatched area. A vertical line labeled 'T1' is also shown.

Symbol	Value(unit:mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2

